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# **ON Semiconductor®** FNB50560T1 Motion SPM<sup>®</sup> 55 Series

# **Features**

• UL Certified No. E209204 (UL1557)

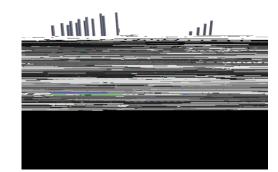
April 2017

# **General Description**

FNB50560T1 is a Motion SPM 55 module providing a

FNB50560T1 Motion SPM® 55 Series • 600 V - 5 A 3-Phase IGBT Inverter Including Contro TJ1.04 -1.22 TD.0017 Tc.00060017tApplications Motion Control

# **Related Resources**



# **Integrated Power Functions**

• 600 V - 5 A IGBT inverter for three phase DC / AC power conversion (Please refer to Figure 3)

# Integrated Drive, Protection and System Control Functions

For inverter high-side IGBTs: gate drive circuit, high-voltage isolated high-speed level shifting control circuit Under-Voltage

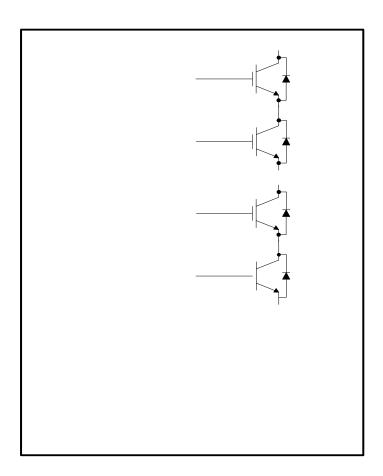
# Pin Descriptions

# Pin Number Pin Name

1	Р
2	U, V <sub>S</sub> (U)
3	V, V <sub>S</sub> (V)
4	W, V <sub>S</sub>

- Positive DC-Link Input Output for U Phase Output for V Phase
- Pin Description

# Internal Equivalent Circuit and Input/Output Pins



### Figure 3. Internal Block Diagram

#### Note:

- 1. Inverter high-side is composed of three IGBTs, freewheeling diodes, and one control IC for each IGBT.
- 2. Inverter low-side is composed of three IGBTs, freewheeling diodes, and one control IC for each IGBT. It has gate drive and protection functions.
- 3. Single drive IC has gate driver for six IGBTs and protection functions.
- 4. Inverter power side is composed of four inverter DC-link input terminals and three inverter output terminals.

# Absolute Maximum Ratings (T<sub>J</sub> = 25°C, unless otherwise specified.)

# **Inverter Part**

Symbol	Parameter	Conditions	Rating	Unit
V <sub>PN</sub>	Supply Voltage	Applied between P - $N_U$ , $N_V$ , $N_W$	450	V
V <sub>PN(Surge)</sub>	Supply Voltage (Surge)	Applied between P - $N_U$ , $N_V$ , $N_W$	500	V
V <sub>CES</sub>	Collector - Emitter Voltage		600	V
± I <sub>C</sub>	Each IGBT Collector Current	$T_{C} = 25^{\circ}C, T_{J} = 150^{\circ}C$	5	А
$\pm I_{CP}$	Each IGBT Collector Current (Peak)	$T_{C} = 25^{\circ}C, T_{J}$ 150°C, Under 1 ms Pulse Width	10	A
P <sub>C</sub>	Collector Dissipation	$T_{C} = 25^{\circ}C$ per Chip	19	W
TJ	Operating Junction Temperature	(Note 5)	-40 ~ 150	°C

#### Note:

5. The maximum junction temperature rating of the power chips integrated within the Motion SPM<sup>®</sup> 55 product is 150°C.

### **Control Part**

Symbol	Parameter	Conditions	Rating	Unit
V <sub>DD</sub>	Control Supply Voltage	Applied between V <sub>DD</sub> - COM	20	V
$V_{BS}$	High-Side Control Bias Voltage	Applied between V_B(U) - V_S(U), V_B(V) - V_S(V), V_B(W) - V_S(W)	20	V
$V_{IN}$	Input Signal Voltage	$\begin{array}{llllllllllllllllllllllllllllllllllll$	-0.3 ~ V <sub>DD</sub> +0.3	V
V <sub>F</sub>	Fault Supply Voltage	Applied between V <sub>F</sub> - COM	-0.3 ~ V <sub>DD</sub> +0.3	V
١ <sub>F</sub>	Fault Current	Sink Current at V <sub>F</sub> pin	5	mA
$V_{SC}$	Current Sensing Input Voltage	Applied between C <sub>SC</sub> - COM	-0.3 ~ V <sub>DD</sub> +0.3	V

### **Total System**

Symbol	Parameter	Conditions	Rating	Unit
V <sub>PN(PROT)</sub>	Self Protection Supply Voltage Limit (Short Circuit Protection Capability)	$V_{DD} = V_{BS} = 13.5 \sim 16.5 \text{ V}$ T <sub>J</sub> = 150°C, Non-Repetitive, < 2 µs	400	V
T <sub>STG</sub>	Storage Temperature		-40 ~ 125	°C
V <sub>ISO</sub>	Isolation Voltage Connect Pins to Heat Sink Plate	AC 60 Hz, Sinusoidal, 1 Minute	1500	V <sub>rms</sub>

### Thermal Resistance

Symbol	Parameter	Conditions	Min.	Тур. Мах.	Unit
P					

R<sub>th(j-c)Q</sub>

Note:

6. For the measurement point of case temperature (T $_{C}$ ), please refer to Figure 2.

<b>Electrical Characteristics</b> ( $T_J = 25^{\circ}C$ , unless otherwise specified	.)
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# Inverter Part

Sy	/mbol	Parameter	Con	ditions	Min.	Тур.	Max.	Unit	
Vo	CE(SAT)	Collector - Emitter Saturation Voltage	$V_{IN} = 5 V$	$T_J = 25^{\circ}C$	-	1.9	2.25	V	
			$I_{C} = 4 A$	T <sub>J</sub> = 150°C		2.4		V	
	V <sub>F</sub>	FWDi Forward Voltage	$V_{IN} = 0 V$	$T_J = 25^{\circ}C$	-	2.2	2.55	V	
		$I_F = 4 A$	$T_J = 150^{\circ}C$		2.0		V		
HS	t <sub>ON</sub>	Switching Times	$V_{PN} = 400 \text{ V}, \text{ V}_{= 400 \text{ V}}$	V V					

Note:

7. t<sub>ON</sub> and t<sub>OFF</sub> include the propagation delay of the internal drive IC. t<sub>C(ON)</sub> and t<sub>C(OFF)</sub> are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.

Figure 4. Switching Time Definition

Symbol	Parameter	Conditions	Conditions		Тур.	Max.	Unit
I <sub>QDD</sub>	Quiescent V <sub>DD</sub> Supply Current	$V_{DD} = 15 \text{ V},$ IN <sub>(UH,VH,WH,UL,VL,WL)</sub> = 0 V	V <sub>DD</sub> - COM	-	2.3	3.4	mA
I <sub>PDD</sub>	Operating V <sub>DD</sub> Supply Current	$V_{DD}$ = 15 V, $f_{PWM}$ = 20 kHz, duty = 50%, applied to one PWM signal input	V <sub>DD</sub> - COM	-	2.7	4.0	mA
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> Supply Current	$V_{BS}$ = 15 V, IN <sub>(UH, VH, WH)</sub> = 0 V	V <sub>B(U)</sub> - V <sub>S(U)</sub> , V <sub>B(V)</sub> - V <sub>S(V)</sub> , V <sub>B(W)</sub> - V <sub>S(W)</sub>	-	60	100	μΑ
I <sub>PBS</sub>	Operating V <sub>BS</sub> Supply Current	$\label{eq:VDD} \begin{array}{l} V_{DD} = V_{BS} = 15 \mbox{ V},  f_{PWM} = 20  kHz, \\ duty = 50\%, \mbox{ applied to one PWM} \\ signal input for high - side \end{array}$		-	250	400	μΑ
$V_{FH}$	Fault Output Voltage	$V_{SC}$ = 0 V, $V_F$ Circuit: 4.7 k $\Omega$ to 5 V	Pull-up	4.5	-	-	V
$V_{FL}$		$V_{SC}$ = 1 V, $V_F$ Circuit: 4.7 k $\Omega$ to 5 V	$V_{SC}$ = 1 V, $V_F$ Circuit: 4.7 k $\Omega$ to 5 V Pull-up		-	0.5	V
V <sub>SC(ref)</sub>	Short-Circuit Trip Level	V <sub>DD</sub> = 15 V (Note 4)		0.45	0.5	0.55	V
UV <sub>DDD</sub>		Detection level		10.0	11.5	13.0	V
$UV_DDR$	Supply Circuit Under-Voltage	Reset level		10.5	12.0	13.5	V
$UV_BSD$	Protection	Detection level		9.5	11.0	12.5	V
$UV_BSR$		Reset level		10.0	11.5	13.0	V
I <sub>FT</sub>	HVIC Temperature Sensing Current	$V_{DD} = V_{BS} = 15 \text{ V}, \text{ T}_{HVIC} = 25^{\circ}\text{C}$		70	95	120	μA
$V_{FT}$	HVIC Temperature Sensing Voltage	V <sub>DD</sub> = V <sub>BS</sub> = 15 V, T <sub>HVIC</sub> = 25°C, 4. (Figure. 5)	7 k $\Omega$ to 5 V Pull-up	-	4.55		V
t <sub>FOD</sub>	Fault-Out Pulse Width			40	100	-	μs
$V_{FSDR}$	Shut-down Reset level	Applied between V <sub>F</sub> - COM		-	-	2.4	V
V <sub>FSDD</sub>	Shut-down Detection level			0.8	-	-	V
V <sub>IN(ON)</sub>	ON Threshold Voltage	Applied between IN(UH), IN(VH), II	$N_{(WH)}$ , $IN_{(UL)}$ , $IN_{(VL)}$ ,	-	-	2.4	V
V <sub>IN(OFF)</sub>	OFF Threshold Voltage	IN <sub>(WL)</sub> - COM		0.8	-	-	V

Note:

8. Short-circuit protection is functioning for all six IGBTs.

Figure. 5. V-T Curve of Temperature Output of IC (5V pull-up with 4.7kohm)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V <sub>PN</sub>	Supply Voltage	Applied between P - $N_U$ , $N_V$ , $N_W$	-	300	400	V
$V_{DD}$	Control Supply Voltage	Applied between V <sub>DD</sub> - COM	14.0	15	16.5	V
$V_{BS}$	High - Side Bias Voltage	Applied between $V_{B(U)}$ - $V_{S(U)}, \; V_{B(V)}$ - $V_{S(V)}, \; V_{B(W)}$ - $V_{S(W)}$	13.0	15	18.5	V
dV <sub>DD</sub> / dt, dV <sub>BS</sub> / dt	Control Supply Variation		-1	-	1	V / μs
t <sub>dead</sub>	Blanking Time for Preventing Arm - Short	For each input signal	0.5	-	-	μs
f <sub>PWM</sub>	PWM Input Signal	- 40°C T <sub>J</sub> 150°C	-	-	20	kHz
V <sub>SEN</sub>	Voltage for Current Sensing	Applied between $N_U$ , $N_V$ , $N_W$ - COM (Including surge voltage)	-4		4	V
P <sub>WIN(ON)</sub>	Minimun Input Pulse Width					

#### Note:

9. This product might not make response if input pulse width is less than the recommanded value.

#### Note:

10. RC coupling at each input (parts shown dotted) might change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board. The input signal section of the SPM 55 product integrates 5 kΩ (typ.) pull-down resistor. Therefore, when using an external filtering resistor, please pay attention to the signal voltage drop at input terminal.

#### Figure 6. Recommended MCU I/O Interface Circuit

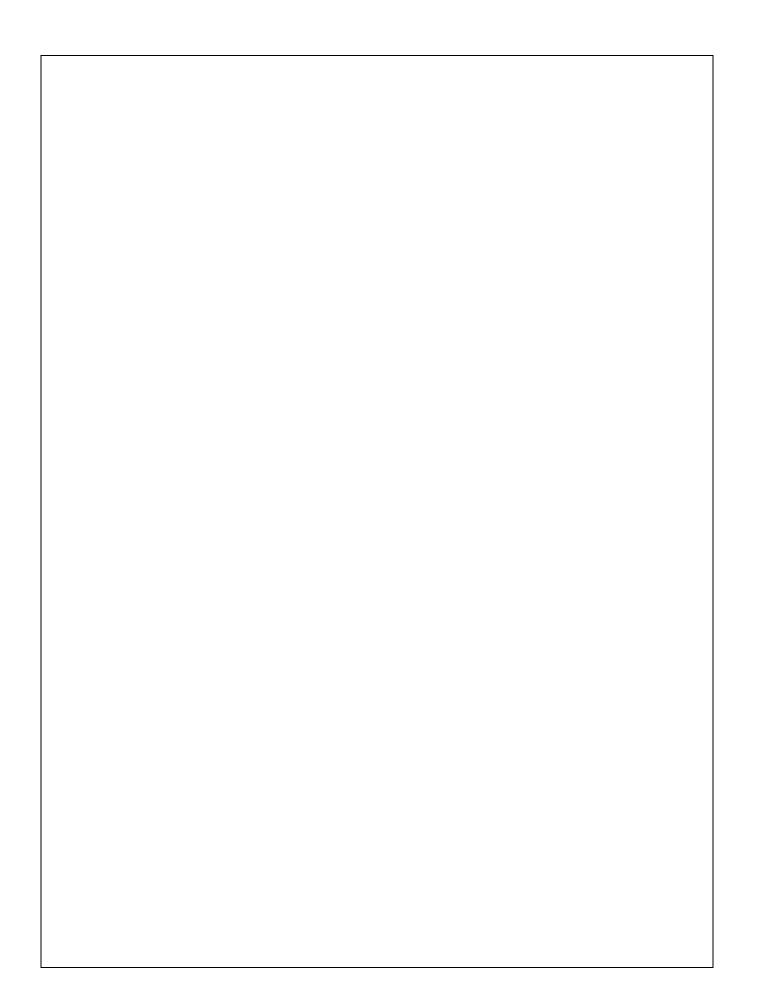
# Mechanical Characteristics and Ratings

### Figure 7. Flatness Measurement Position

# Figure 8. Mounting Screws Torque Order

Note:

11. Do not make over torque when mounting screws. Much mounting torque may cause package cracks, as well as bolts and Al heat-sink destruction.



(with the external shunt resistance and CR connection)

- c1 : Normal operation: IGBT ON and carrying current.
- c2 : Short circuit current detection (SC trigger).
- c3 : Hard IGBT gate interrupt.
- c4 : IGBT turns OFF.
- c5 : Input "L" : IGBT OFF state.
- c6 : Input "H": IGBT ON state, but during the acti

#### Note:

1) To avoid malfunction, the wiring of each input should be as short as possible. (less than 2 ~ 3 cm)

2) By virtue of integrating an application specific type of HVIC inside the SPM<sup>®</sup> 55 product, direct coupling to MCU terminals without any opto-coupler or transformer isolation is possible.

3) V<sub>F</sub> is open-drain type. This signal line should be pulled up to the positive side of the MCU or control power supply with a resistor that makes I<sub>FO</sub> up to 5 mA. Please refer to Figure 14.

4)  $C_{\text{SP15}}$  of around seven times larger than bootstrap capacitor  $C_{\text{BS}}$  is recommended.

5) Input signal is active-HIGH type. There is a 5 k $\Omega$  resistor inside the IC to pull down each input signal line to GND. RC coupling circuits is recommanded for the prevention of input signal oscillation. R<sub>S</sub>C<sub>PS</sub> time constant should be selected in the range 50 ~ 150 ns. (Recommended R<sub>S</sub> = 100 , C<sub>PS</sub> = 1 nF)

6) To prevent errors of the protection function, the wiring around  $\rm R_{F}$  and  $\rm C_{SC}$ 

Detailed Package Outline Drawings (FNB51060T1, Short Lead)

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or data on the drawing and contact a FairchildSemiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide therm and conditions, specifically the the warranty therein, which covers Fairchild products.

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